

CMOS 16384-Bit Static Random Access Memory

LH5116-15/-20

T-46-23-12

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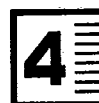
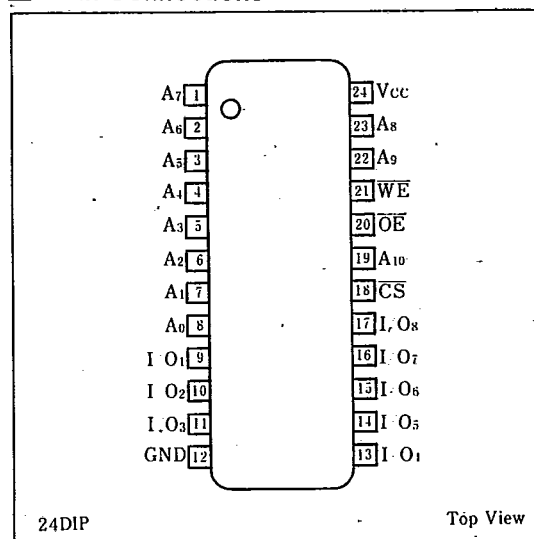
Description

The LH5116-15/-20 are fully static RAMs organized as 2,048×8-bit by using silicon-gate CMOS process technology.

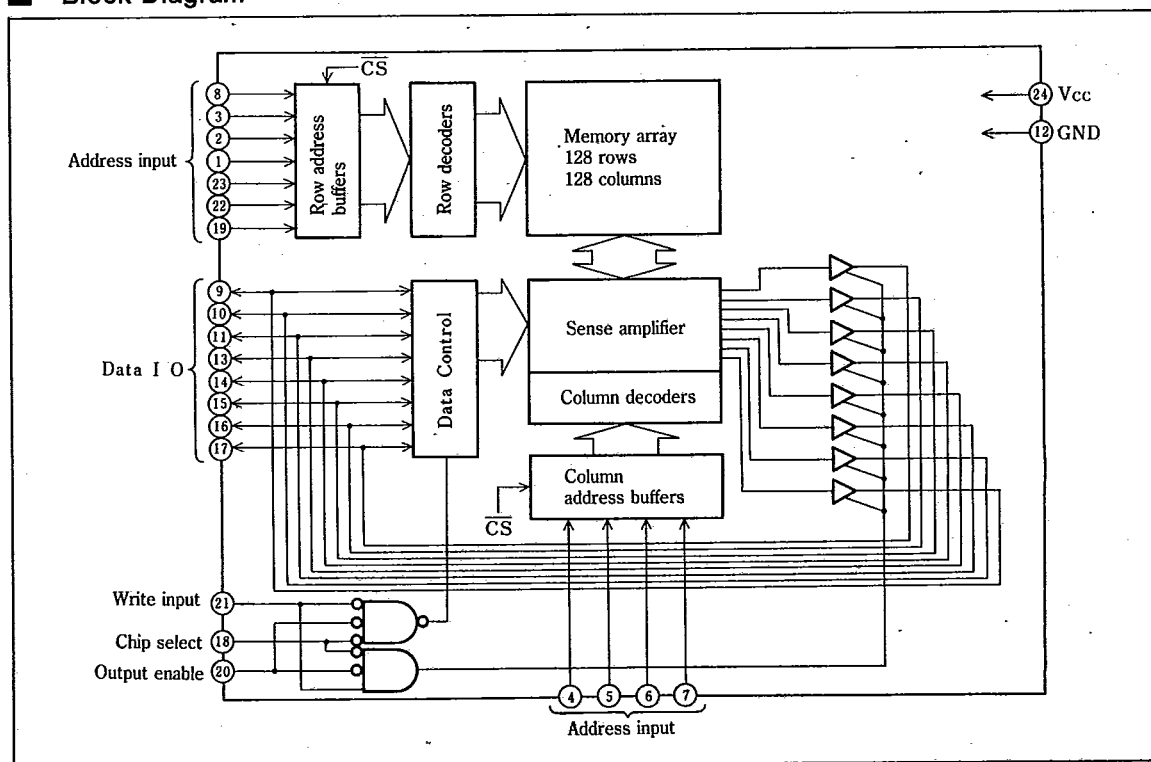
Features

1. 2,048×8-bit organization
2. Single +5V power supply
3. Fully static operation
4. All inputs and outputs TTL compatible
5. Three-state outputs
6. Access time (MAX.)
LH5116-15 : 150ns, LH5116-20 : 200ns
7. Supply current at standby mode 1 μ A (MAX.) on +2V supply voltage
8. 24-pin dual-in-line package

Pin Connections



Block Diagram



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■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit	Note
Supply voltage	V_{CC}	$-0.3 \sim +7.0$	V	1
Input voltage	V_{IN}	$-0.3 \sim V_{CC} + 0.3$	V	1
Operating temperature	T_{opr}	$0 \sim +70$	°C	
Storage temperature	T_{stg}	$-55 \sim +150$	°C	

Note 1: The maximum applicable voltage on any pin with respect to GND.

■ DC Characteristics

 $(V_{CC} = 5V \pm 10\%, T_a = 0 \sim +70^\circ C)$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Note
Input low voltage	V_{IL}		-0.3		0.8	V	
Input high voltage	V_{IH}		2.2		$V_{CC} + 0.3$	V	
Output low voltage	V_{OL}	$I_{OL} = 2.1mA$			0.4	V	
Output high voltage	V_{OH}	$I_{OH} = -1.0mA$	2.4			V	
Input leakage current	$ I_{LI} $	$V_{IN} = 0V, V_{CC}$			1.0	μA	
Output leakage current	$ I_{LO} $	$\overline{CS} = V_{IH}, V_{I/O} = 0V \sim V_{CC}$			1.0	μA	
Current consumption	I_{CC1}	$I_{I/O} = 0mA (OE = V_{CC})$		15	30	mA	1
	I_{CC2}	$I_{I/O} = 0mA (OE = V_{IH})$		25	40	mA	2
Current consumption during standby	I_{CCL}	$CS = V_{CC}, \text{all other input pins} = 0V \sim V_{CC}$			1	μA	

Note 1: $\overline{CS} = 0V$; all other input pins = V_{CC} Note 2: $CS = V_{IH}$; all other input pins = V_{IH}

■ AC Characteristics

(1) Read cycle

 $(V_{CC} = 5V \pm 10\%, T_a = 0 \sim +70^\circ C)$

Parameter	Symbol	LH5116-15			LH5116-20			Unit
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Cycle time	t_{RC}	150			200			ns
Access time	t_{ACC}			150			200	ns
Chip enable time	t_{CE}			150			200	ns
Chip select time	t_{CS}	15			20			ns
Output enable access time	t_{OE}			75			100	ns
Output select time	t_{OS}	15			20			ns
Output turn-off time (from $\overline{CE}_2$)	t_{DF1}	0		40	0		60	ns
Output turn-off time (from $\overline{CE}_1$)	t_{DF2}	0		40	0		60	ns
Data hold time	t_{OH}	15			20			ns

(2) Write cycle

 $(V_{CC} = 5V \pm 10\%, T_a = 0 \sim 70^\circ C)$

Parameter	Symbol	LH5116-15			LH5116-20			Unit
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Cycle time	t_{WC}	150			200			ns
Chip select time	t_{CW}	110			135			ns
Access time	t_{AW}	110			135			ns
Address setup time	t_{AS}	0			5			ns
Pulse width	t_{WP}	110			140			ns
Recovery time	t_{WR}	20			35			ns
Output floating time from OE	t_{DF1}			40			60	ns
Data setup time	t_{DW}	70			80			ns
Data hold time	t_{DH}	10			10			ns
Output active time from WE	t_{OW}	15			20			ns
Output floating time from OE	t_{DF2}			40			60	ns

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- Test conditions of AC characteristics
- Input voltage amplitude0.8~2.2V
 - Input rise/fall time10ns
 - Timing reference level1.5V
 - Output load condition1TTL+100pF

Low Voltage Data Hold Characteristics (V_{CC}=5V±10%, Ta=0~+70℃)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage for data hold	V _{CCDR}	V _{CS} =V _{CC} , V _{IN} =0V or V _{CC}	2.0			V
Supply current for data hold	I _{CCDR}	V _{CC} =V _{CS} =2.0V, V _{IN} =0V or V _{CC}			1	μA
CS setup time	t _{SDR}		t _{RC}			ns
CS hold time	t _{RDR}		t _{RC}			ns

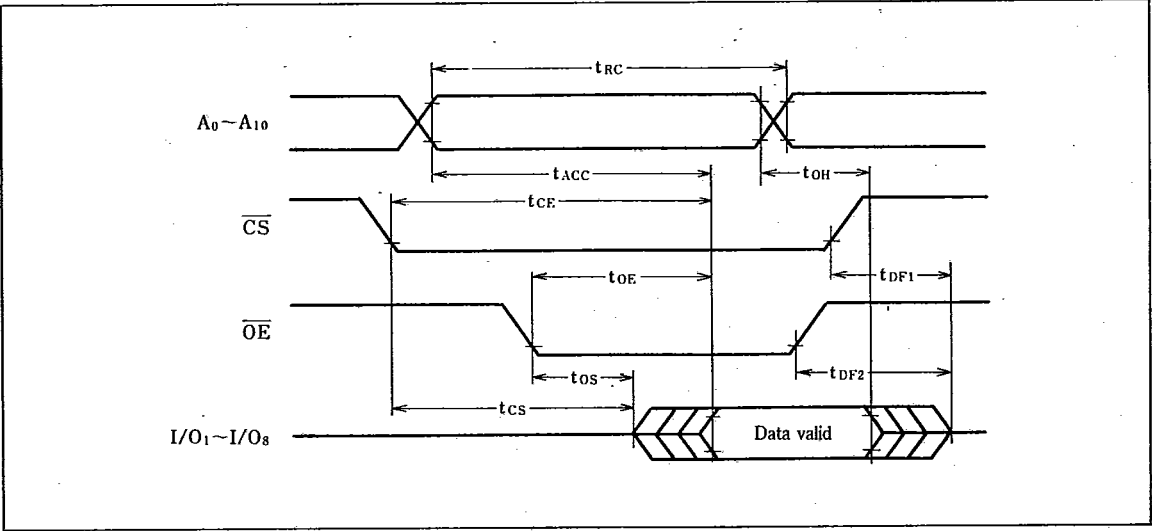
Capacitance (f=1MHz, Ta=25℃)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C _{IN}	V _{IN} =0V			5	pF
Input/output capacitance	C _{I/O}	V _{I/O} =0V			8	pF

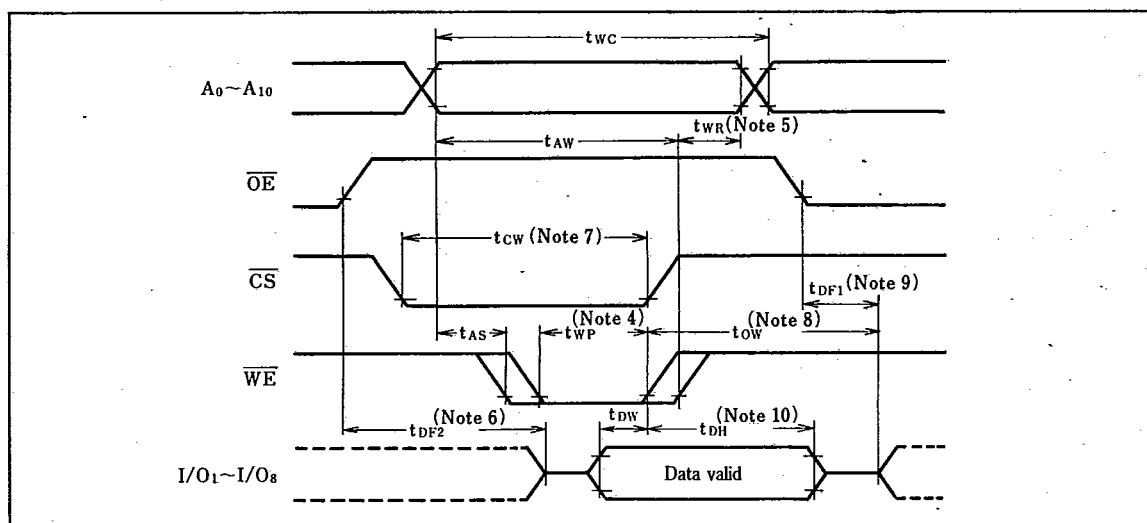


Timing Diagram

(1) Read cycle



(2) Write cycle (Note 3)



Note 3: $\overline{WE}$ must be high when there is a change in $A_0 \sim A_{10}$.

Note 4: When $\overline{CS}$ and $\overline{WE}$ are all low at the same time, write occurs during the period t_{WP} .

Note 5: t_{WR} is the time from the rise of $\overline{CS}$ or $\overline{WE}$, whichever is first, to the end of the write cycle.

Note 6: During this period the input/output pin is in an output condition, so input with a phase reversed from that of the output is not permitted.

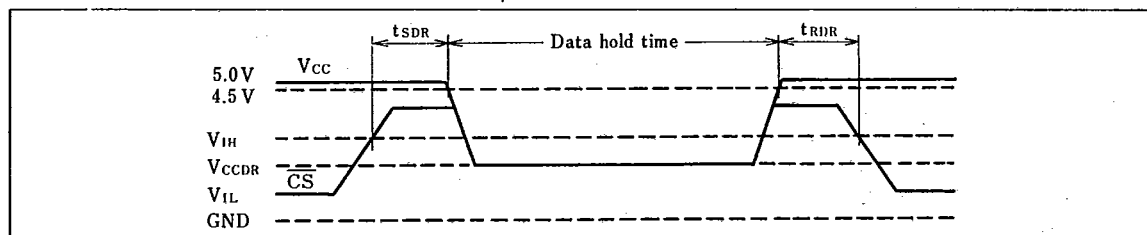
Note 7: If $\overline{CS}$ should drop at the same time as $\overline{WE}$ or later, the output buffer is maintained at high impedance.

Note 8: $\overline{OE}$ is maintained at "L" level.

Note 9: Data outputs data with the same phase as the input data of this write cycle.

Note 10: If $\overline{CS}$ is low during this period, the input/output pin is in the output condition. During this condition, a data input signal with a phase opposite that of the output is not permitted.

(3) Low voltage data hold



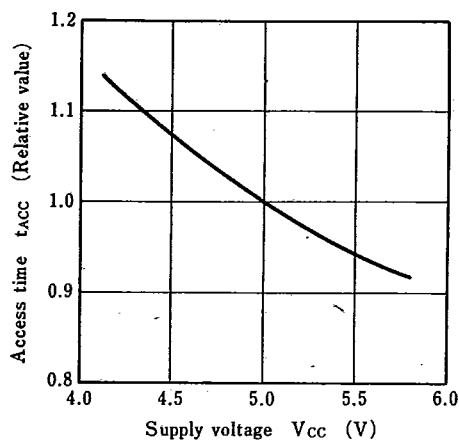
Pin Description

Signal	Pin name
$A_0 \sim A_{10}$	Address input
$\overline{CS}$	Chip select
$\overline{OE}$	Output enable
$\overline{WE}$	Write enable
$I/O_1 \sim I/O_8$	Data input/output
V_{CC}	Power supply
GND	Ground

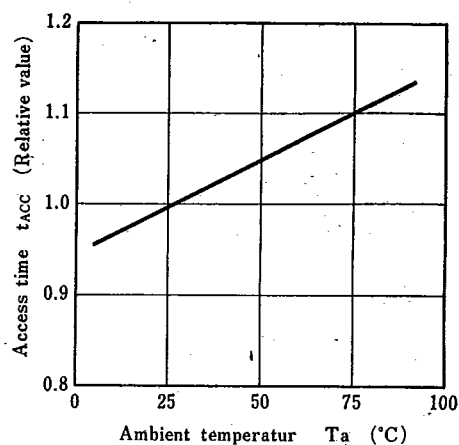
CS	OE	WE	Mode	$I/O_1 \sim I/O_8$	Supply current
L	X	L	Write	D_{IN}	Operation (I_{CC})
L	L	H	Read	D_{OUT}	Operation (I_{CC})
H	X	X	Deselect	High Z	Standby (I_{CC1})
L	H	X	Output disable	High Z	Operation (I_{CC})

■ Electrical Characteristics Curves ($V_{CC}=5V$, $T_a=25^\circ C$ unless otherwise specified)

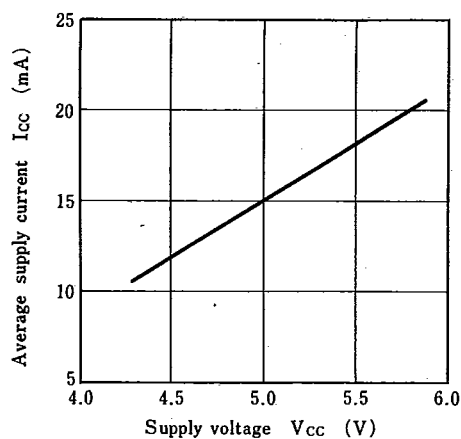
Access time vs. supply voltage



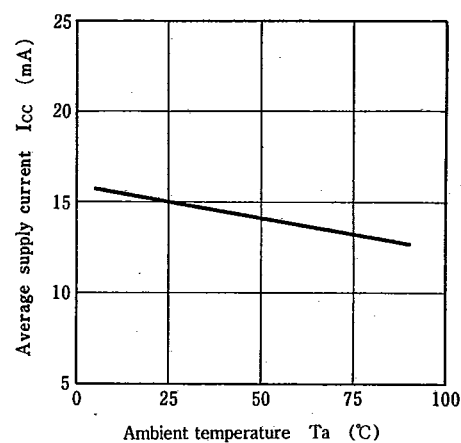
Access time vs. ambient temperature



Average supply current vs. supply voltage

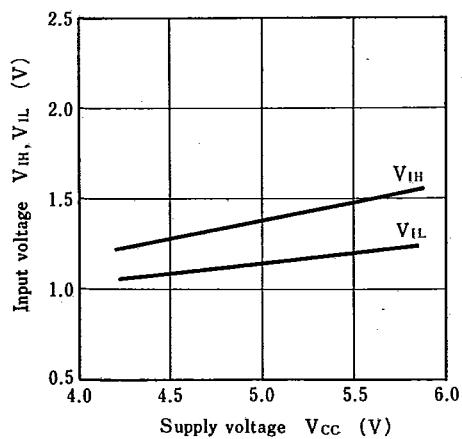


Average supply current vs. ambient temperature

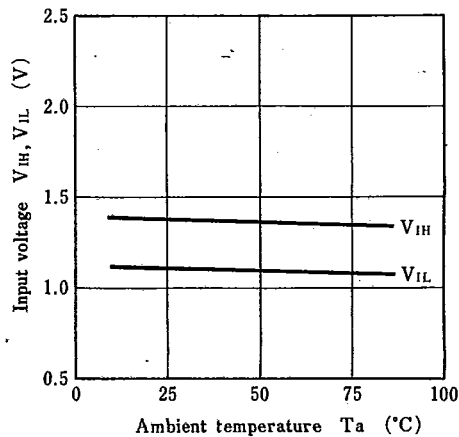


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Input voltage vs. supply voltage



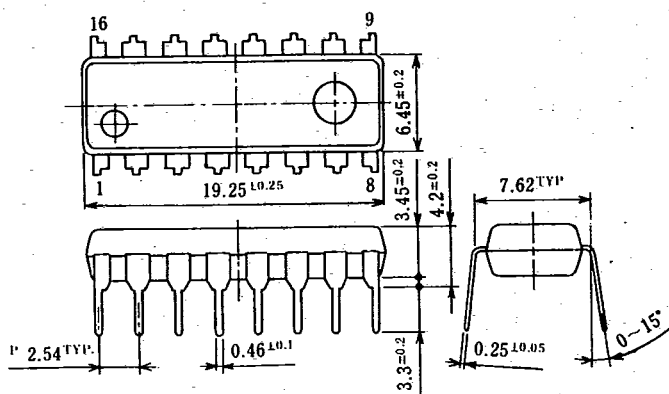
Input voltage vs. ambient temperature



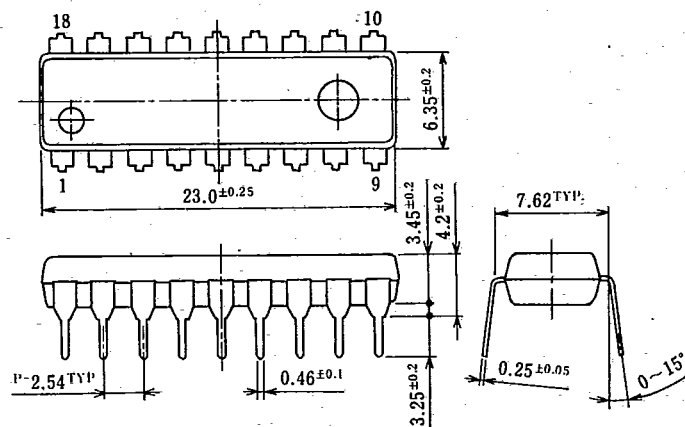
Package Outline (Unit:mm)

T-90-20

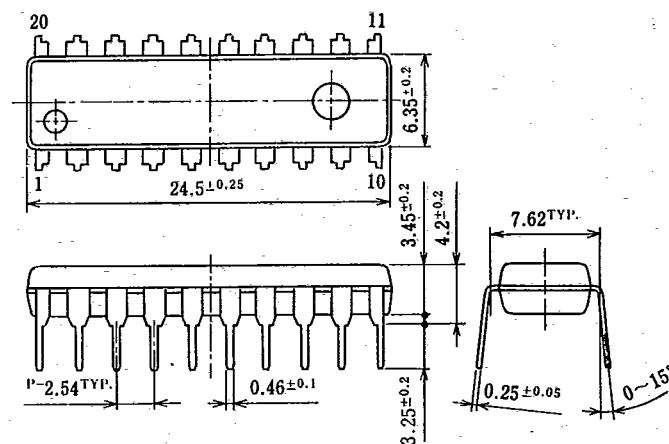
16DIP



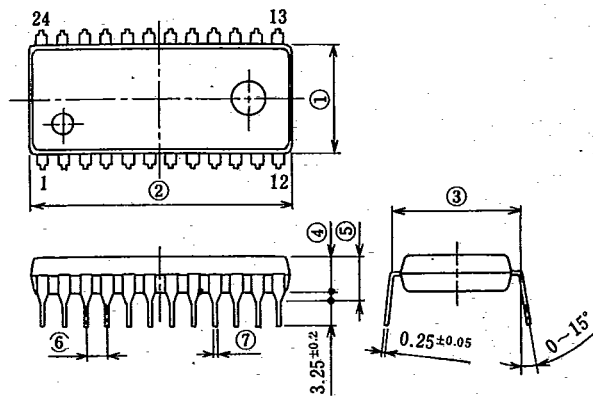
18DIP



20DIP

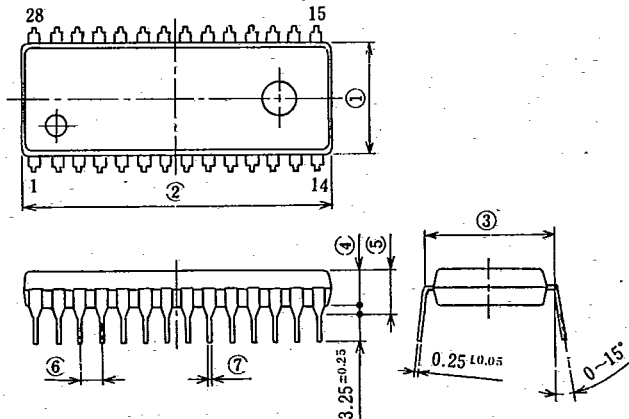


24DIP



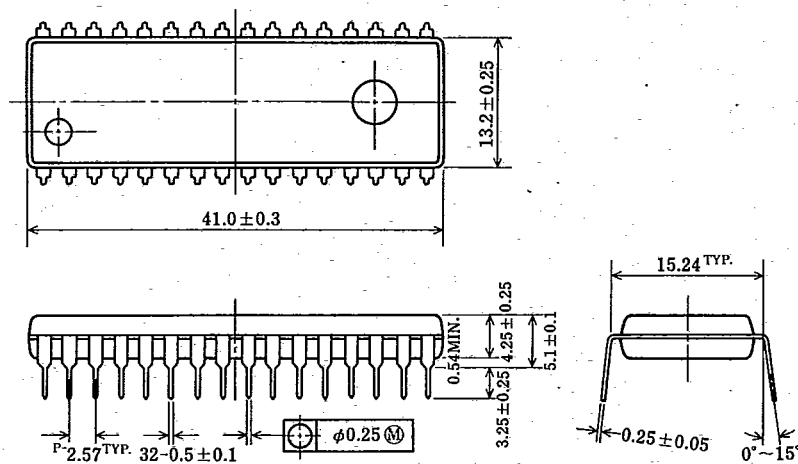
	Normal	Shrink
①	13.2±0.25	6.35±0.2
②	31.0±0.3	22.0±0.25
③	15.24 TYP.	7.62 TYP.
④	4.25±0.2	3.45±0.2
⑤	5.1±0.2	4.2±0.2
⑥	P-2.54 TYP.	P-1.778 TYP.
⑦	0.5±0.1	0.46±0.1

28DIP

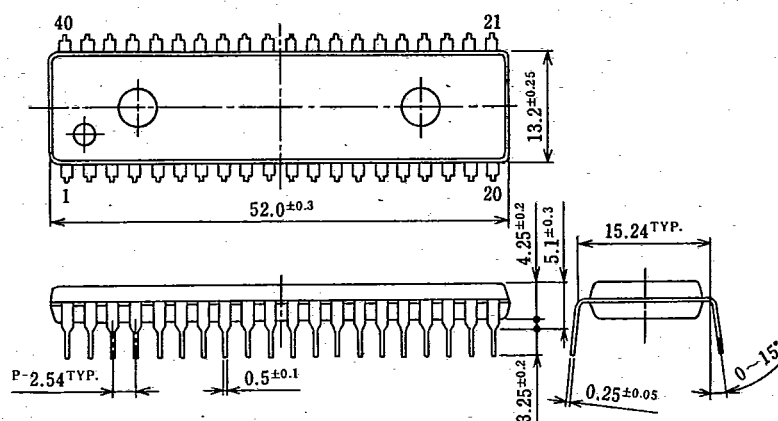


	Normal	Shrink
①	13.2±0.25	8.6±0.2
②	36.0±0.3	25.5±0.25
③	15.24 TYP.	10.16 TYP.
④	4.25±0.25	3.85±0.2
⑤	5.1±0.2	4.4±0.2
⑥	P-2.54 TYP.	P-1.778 TYP.
⑦	0.5±0.1	0.46±0.1

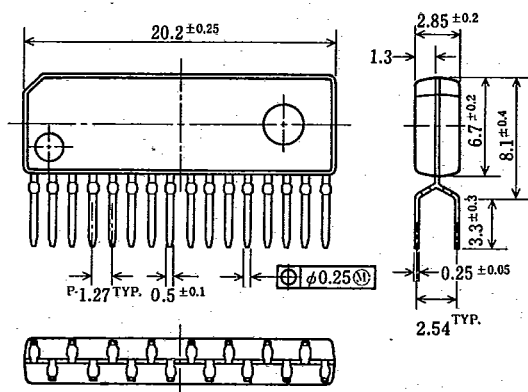
32DIP



40DIP

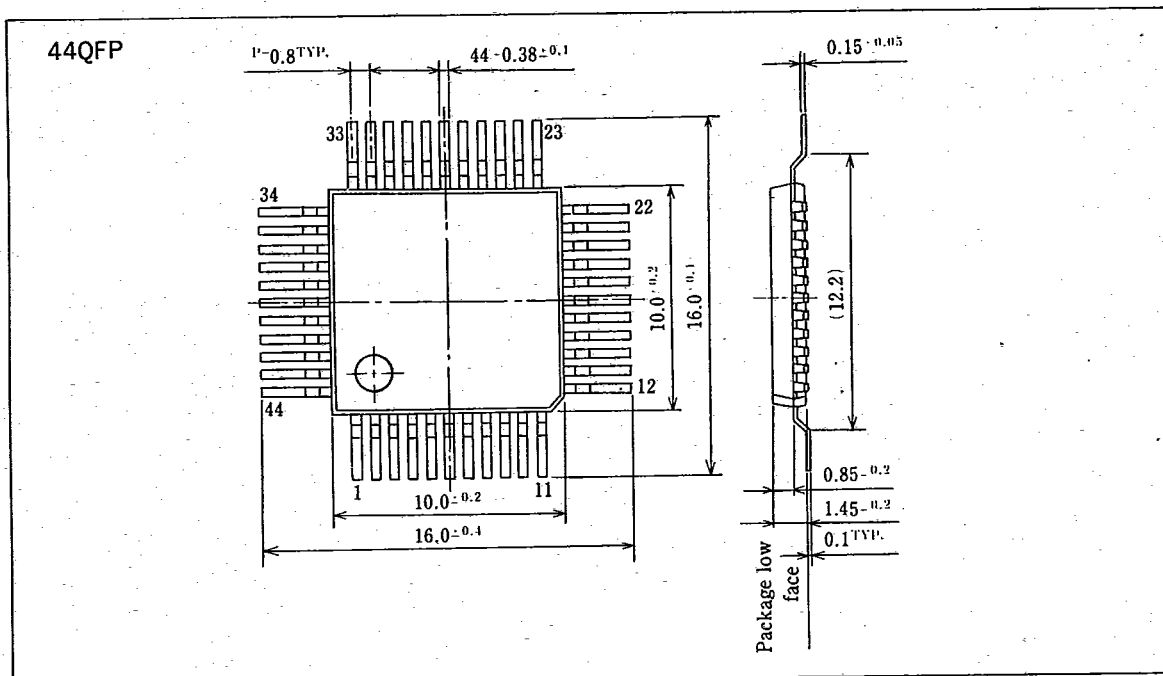


16ZIP



Package Outline

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